ADVISORY PRODUCT CHANGE NOTICE

Product Group: Vishay Siliconix/ November 17th, 2021 - A**PCN-SIL-5022021**

SIC461-4 and SIC471-4 Datasheet Changes

DESCRIPTION OF CHANGE: Correction of the minimum VDRV Supply voltage from 5.1V to 4.75V, and Maximum VDRV current from 50mA to 30mA. Datasheets change on Page 4.

CLASSIFICATION OF CHANGE: Datasheet

REASON FOR CHANGE: Correction

EXPECTED INFLUENCE ON PERFORMANCE/QUALITY/RELIABILTY: There will be no effect on performance, quality or reliability.

PRODUCT CATAGORY: ICs

PART NUMBERS AFFECTED: SIC461ED-T1-GE3, SIC462ED-T1-GE3, SIC463ED-T1-GE3, SIC464ED-T1-GE3, SIC471ED-T1-GE3, SIC472ED-T1-GE3, SIC473ED-T1-GE3, SIC474ED-T1-GE3

VISHAY BRAND(s): Vishay-Siliconix

TIME SCHEDULE: Immediately, November 17, 2021

SAMPLE AVAILABILITY: Samples available immediately

QUALIFICATION DATA: See details in attachment

This APCN is for notification purposes only. Your response is not required. If you have any questions, please contact your local Vishay Sales Office.

ISSUED BY: Isabelle Ciacchella, Vishay Siliconix IC Product Marketing.
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For further information, please contact your regional Vishay office.

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SIC461/2/3/4 Datasheet – Doc#65124

Revision O – March 2021

ELECTRICAL SPECIFICATIONS (V_{IN} = V_{CIN} = 48 V, V_{EN} = 5 V, T_J = -40 °C to +125 °C, unless otherwise stated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Power Supplies						
V_{DD} supply	V_{DD}	V_{IN} = V_{CIN} = 6 V to 60 V	4.75	5	5.25	V
		V_{IN} = V_{CIN} = 5 V	4.7	5	-	
V_{DD} dropout	$V_{DD\_DROPOUT}$	V_{IN} = V_{CIN} = 5 V, I_{VDD} = 1 mA	-	70	-	mV
V_{DD} UVLO threshold, rising	V_{DD_UVLO}		4	4.25	4.5	V
V_{DD} UVLO hysteresis	$V_{DD\_UVLO\_HYST}$		-	225	-	mV
Maximum V_{DD} current	I_{DD}	V_{IN} = V_{CIN} = 6 V to 60 V	3	-	-	mA
V_{DRV} supply	V_{DRV}	V_{IN} = V_{CIN} = 6 V to 60 V	5.1	5.3	5.55	V
		V_{IN} = V_{CIN} = 5 V	4.8	5	5.2	
V_{DRV} dropout	$V_{DRV\_DROPOUT}$	V_{IN} = V_{CIN} = 5 V, I_{VDD} = 10 mA	-	160	-	mV
Maximum V_{DRV} current	V_{DRV}	V_{IN} = V_{CIN} = 6 V to 60 V	50	-	-	mA
V_{DRV} UVLO threshold, rising	V_{DRV_UVLO}		4	4.25	4.5	V
V_{DRV} UVLO hysteresis	$V_{DRV\_UVLO\_HYST}$		-	295	-	mV
Input current	I_{VCIN}	Non-switching, V_{FB} > 0.8 V	-	235	325	µA
Shutdown current	I_{VCIN_SHDN}	V_{FN} = 0 V	-	4	8	

Revision P – November 2021

ELECTRICAL SPECIFICATIONS (V_{IN} = V_{CIN} = 48 V, V_{EN} = 5 V, T_J = -40 °C to +125 °C, unless otherwise stated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Power Supplies						
V_{DD} supply	V_{DD}	V_{IN} = V_{CIN} = 6 V to 60 V	4.75	5	5.25	V
		V_{IN} = V_{CIN} = 5 V	4.7	5	-	
V_{DD} dropout	$V_{DD\_DROPOUT}$	V_{IN} = V_{CIN} = 5 V, I_{VDD} = 1 mA	-	70	-	mV
V_{DD} UVLO threshold, rising	V_{DD_UVLO}		4	4.25	4.5	V
V_{DD} UVLO hysteresis	$V_{DD\_UVLO\_HYST}$		-	225	-	mV
Maximum V_{DD} current	I_{DD}	V_{IN} = V_{CIN} = 6 V to 60 V	3	-	-	mA
V_{DRV} supply	V_{DRV}	V_{IN} = V_{CIN} = 6 V to 60 V	4.75	5.3	5.55	V
		V_{IN} = V_{CIN} = 5 V	4.8	5	5.2	
V_{DRV} dropout	$V_{DRV\_DROPOUT}$	V_{IN} = V_{CIN} = 5 V, I_{VDD} = 10 mA	-	160	-	mV
Maximum V_{DRV} current	V_{DRV}	V_{IN} = V_{CIN} = 6 V to 60 V	30	-	-	mA
V_{DRV} UVLO threshold, rising	V_{DRV_UVLO}		4	4.25	4.5	V
V_{DRV} UVLO hysteresis	$V_{DRV\_UVLO\_HYST}$		-	295	-	mV
Input current	I_{VCIN}	Non-switching, V_{FB} > 0.8 V	-	235	325	µA
Shutdown current	I_{VCIN_SHDN}	V_{EN} = 0 V	-	4	8	

Vishay Intertechnology, Inc.

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ONE OF THE WORLD'S LARGEST MANUFACTURERS OF DISCRETE SEMICONDUCTORS AND PASSIVE COMPONENT

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ADVISORY PRODUCT CHANGE NOTICE

SIC471/2/3/4 Datasheet – Doc#75786

Revision F – March 2021

ELECTRICAL SPECIFICATIONS ($V_{IN} = V_{CIN} = 48$ V, $V_{EN} = 5$ V, $T_J = -40$ °C to $+125$ °C, unless otherwise stated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Power Supplies						
V_{DD} supply	V_{DD}	$V_{IN} = V_{CIN} = 6$ V to 55 V	4.75	5	5.25	V
		$V_{IN} = V_{CIN} = 5$ V	4.7	5	-	
V_{DD} dropout	$V_{DD\_DROPOUT}$	$V_{IN} = V_{CIN} = 5$ V, $I_{VDD} = 1$ mA	-	70	-	mV
V_{DD} UVLO threshold, rising	V_{DD_UVLO}		4	4.25	4.5	V
V_{DD} UVLO hysteresis	$V_{DD\_UVLO\_HYST}$		-	225	-	mV
Maximum V_{DD} current	I_{DD}	$V_{IN} = V_{CIN} = 6$ V to 55 V	3	-	-	mA
V_{DRV} supply	V_{DRV}	$V_{IN} = V_{CIN} = 6$ V to 55 V	5.1	5.3	5.55	V
		$V_{IN} = V_{CIN} = 5$ V	4.8	5	5.2	
V_{DRV} dropout	$V_{DRV\_DROPOUT}$	$V_{IN} = V_{CIN} = 5$ V, $I_{VDD} = 10$ mA	-	160	-	mV
Maximum V_{DRV} current	V_{DRV}	$V_{IN} = V_{CIN} = 6$ V to 55 V	50	-	-	mA
V_{DRV} UVLO threshold, rising	V_{DRV_UVLO}		4	4.25	4.5	V
V_{DRV} UVLO hysteresis	$V_{DRV\_UVLO\_HYST}$		-	295	-	mV
Input current	I_{VCIN}	Non-switching, $V_{FB} > 0.8$ V	-	235	325	μA
Shutdown current	I_{VCIN_SHDN}	$V_{EN} = 0$ V	-	4	8	

Revision G – November 2021

ELECTRICAL SPECIFICATIONS ($V_{IN} = V_{CIN} = 48$ V, $V_{EN} = 5$ V, $T_J = -40$ °C to $+125$ °C, unless otherwise stated)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Power Supplies						
V_{DD} supply	V_{DD}	$V_{IN} = V_{CIN} = 6$ V to 55 V	4.75	5	5.25	V
		$V_{IN} = V_{CIN} = 5$ V	4.7	5	-	
V_{DD} dropout	$V_{DD\_DROPOUT}$	$V_{IN} = V_{CIN} = 5$ V, $I_{VDD} = 1$ mA	-	70	-	mV
V_{DD} UVLO threshold, rising	V_{DD_UVLO}		4	4.25	4.5	V
V_{DD} UVLO hysteresis	$V_{DD\_UVLO\_HYST}$		-	225	-	mV
Maximum V_{DD} current	I_{DD}	$V_{IN} = V_{CIN} = 6$ V to 55 V	3	-	-	mA
V_{DRV} supply	V_{DRV}	$V_{IN} = V_{CIN} = 6$ V to 55 V	4.75	5.3	5.55	V
		$V_{IN} = V_{CIN} = 5$ V	4.8	5	5.2	
V_{DRV} dropout	$V_{DRV\_DROPOUT}$	$V_{IN} = V_{CIN} = 5$ V, $I_{VDD} = 10$ mA	-	160	-	mV
Maximum V_{DHV} current	V_{DHV}	$V_{IN} = V_{CIN} = 6$ V to 55 V	30	-	-	mA
V_{DRV} UVLO threshold, rising	V_{DRV_UVLO}		4	4.25	4.5	V
V_{DRV} UVLO hysteresis	$V_{DRV\_UVLO\_HYST}$		-	295	-	mV
Input current	I_{VCIN}	Non-switching, $V_{FB} > 0.8$ V	-	235	325	μA
Shutdown current	I_{VCIN_SHDN}	$V_{EN} = 0$ V	-	4	8	

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